

N.D. Il'inskaya, S.A. Karandashev, A.A. Lavrov, B.A. Matveev, M.A. Remennyi, N.M. Stus', A.A. Usikova,

"P-InAsSbP/p- InAs_{0.88}Sb_{0.12}/n- InAs_{0.88}Sb_{0.12}/n + -InAs PDs with a smooth p-n junction"

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Annotation

Current-voltage, capacitance-voltage, and photoelectrical characteristics of InAs_{0.88}Sb_{0.12} photodiodes grown onto InAs substrates with a smooth p-n junction and various mesa diameters and layer thicknesses sensitive to radiation with wavelengths up to 5.5 μm were investigated and analyzed. Conclusions on the impact of the InAs_{0.88}Sb_{0.12}-layer thickness on the main performance parameters (zero bias resistance, sensitivity, and spectral response) are presented and discussed.